4.4 Summary

4.4.1 Summary to: 4. Getting Started









GaAs:

150 mm wafers, encapsulation technique, disl. density $(10^3 - 10^6)$ cm⁻²

GaP, InP as GaAs but smaller and more expensive

SiC: 100 mm wafers, sublimation technique, several polytypes available, "pipe" defects

